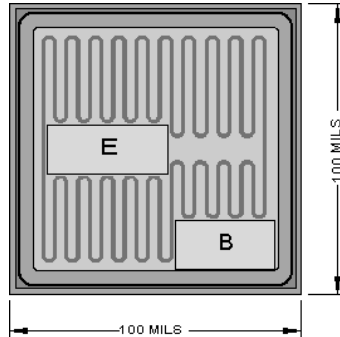


**Chip Type 2C5664**  
**Geometry 9221**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N5664, 2N5666**



[Request Quotation](#)

Chip type **2C5664** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**  
 2N5664, 2N5666

**Product Summary:**

**APPLICATIONS:** Designed for high voltage, high speed switching and power amplifier applications.

**Features:**

- High voltage ratings

Mechanical Specifications		
Metallization	Top	Al - 37.5 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	12 mils x 40 mils
	Base	12 mils x 30 mils
Die Thickness	8 mils nominal	
Chip Area	100 mils x 100 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CER}$	$I_C = 10 \text{ mA}$ , $R = 100 \text{ ohms}$	250	---	V dc
$BV_{EBO}$	$I_E = 10 \text{ }\mu\text{A}$	6.0	---	$\mu\text{A}$
$I_{CES}$	$V_{CE} = 200 \text{ V}$ , $I_E = 0$	---	0.2	$\mu\text{A}$
$h_{FE}$	$I_C = 500 \text{ mA dc}$ , $V_{CE} = 2.0 \text{ V}$	50	---	---
$h_{FE}$	$I_C = 1.0 \text{ A dc}$ , $V_{CE} = 5.0 \text{ V}$	25	75	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*